



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

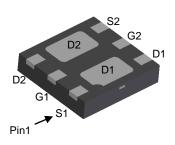
Product Summary

| V _{(BR)DSS} | R _{DS(ON)} max | I _D max T _A = +25°C |
|----------------------|--------------------------------|--|
| 001/ | 50mΩ @V _{GS} = -4.5V | -4.5A |
| -20V | 100mΩ @V _{GS} = -2.5V | -3.2A |

Description and Applications

This MOSFET has been designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- **Battery Charging**
- **Power Management Functions**
- **DC-DC Converters**
- Portable Power Adaptors



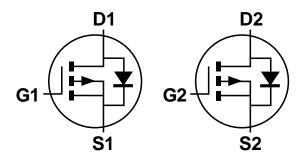
Bottom View

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: U-DFN2020-6 (Type B)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)



Internal Schematic

Ordering Information (Note 4)

| Part Number | Case | Packaging | | |
|----------------|----------------------|--------------------|--|--|
| DMP2065UFDB-7 | U-DFN2020-6 (Type B) | 3,000/Tape & Reel | | |
| DMP2065UFDB-13 | U-DFN2020-6 (Type B) | 10,000/Tape & Reel | | |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



P5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: D = 2016)M = Month (ex: 9 = September)

Date Code Key

| Year | 201 | 5 | 2016 | | 2017 | 20 | 18 | 2019 | | 2020 | 2 | 2021 | |
|-------|-----|-----|------|-----|------|-----|-----|------|-----|------|-----|------|--|
| Code | С | | D | | E | | = | G | | Н | | I | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec | |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D | |



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | | Symbol | Value | Units | |
|---|-----------------|------------------|-----------------|-------|---|
| Drain-Source Voltage | | V_{DSS} | -20 | V | |
| Gate-Source Voltage | | V _{GSS} | ±12 | V | |
| Continuous Drain Current (Note 6) V _{GS} = -4.5V | Steady State | l _D | -4.5 -3.6 | А | |
| Pulsed Drain Current (10µs pulse, duty cycle = 1 | %) | | I _{DM} | -25 | Α |
| Maximum Continuous Body Diode Forward Curre | ent (Note 6) | Is | -1.4 | Α | |
| Avalanche Current (Note 7) L = 0.1mH | | I _{AS} | -13 | Α | |
| Avalanche Energy (Note 7) L = 0.1mH | | E _{AS} | 9 | mJ | |

Thermal Characteristics

| Characteristic | Symbol | Value | Units | | |
|--|------------------------|----------------------------------|-------------|------|--|
| Total Power Dissipation (Note 5) | T _A = +25°C | P _D | 0.74 | W | |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady state | D | 171 | °C/W | |
| Thermal Resistance, Junction to Ambient (Note 5) | t<10s | $R_{\theta JA}$ | 131 | | |
| Total Power Dissipation (Note 6) | T _A = +25°C | P _D | 1.54 | W | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state | D | 82 | | |
| Thermal Resistance, Junction to Ambient (Note 6) | t<10s | $R_{\theta JA}$ | 60 | °C/W | |
| Thermal Resistance, Junction to Case (Note 6) | R ₀ JC | 13 | | | |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -55 to +150 | °C | |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

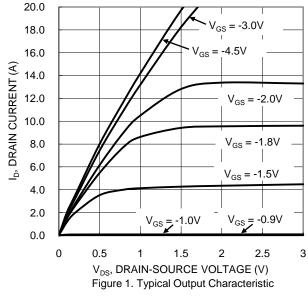
| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|------|-------|------|-------|---|--|
| OFF CHARACTERISTICS (Note 8) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -20 | | | V | $V_{GS} = 0V, I_D = -250\mu A$ | |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | | _ | -1.0 | μΑ | $V_{DS} = -20V, V_{GS} = 0V$ | |
| Gate-Source Leakage | I _{GSS} | | | ±100 | nA | $V_{GS} = \pm 8V$, $V_{DS} = 0V$ | |
| ON CHARACTERISTICS (Note 8) | | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | -0.4 | _ | -1.0 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | |
| | | | 40 | 50 | | $V_{GS} = -4.5V, I_D = -2.0A$ | |
| Static Drain-Source On-Resistance | D | | 55 | 100 | mΩ | $V_{GS} = -2.5V, I_D = -2.0A$ | |
| Static Dialit-Source Off-Resistance | R _{DS(ON)} | _ | 75 | 150 | 11122 | $V_{GS} = -1.8V$, $I_D = -1.6A$ | |
| | | | 95 | 200 | | $V_{GS} = -1.5V, I_D = -1.0A$ | |
| Diode Forward Voltage | V_{SD} | | -0.75 | -1.1 | V | $V_{GS} = 0V$, $I_S = -1A$ | |
| DYNAMIC CHARACTERISTICS (Note 9) | | | | | | | |
| Input Capacitance | Ciss | | 752 | _ | pF | \\\ 45\\\\\\ 0\\\ | |
| Output Capacitance | Coss | | 87 | _ | рF | $V_{DS} = -15V, V_{GS} = 0V$ -f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | | 78 | _ | рF | 1 = 1.0WH2 | |
| Gate Resistance | R_{G} | | 15.2 | _ | Ω | $V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1.0MHz$ | |
| Total Gate Charge | Q_{g} | | 9.1 | | nC | \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\ | |
| Gate-Source Charge | | | 1.2 | _ | nC | $V_{GS} = -4.5V, V_{DS} = -4V,$ $I_{D} = -3.5A$ | |
| Gate-Drain Charge | Q_{gd} | | 1.9 | | nC | ID = -3.5A | |
| Turn-On Delay Time | | | 5.4 | _ | ns | | |
| Turn-On Rise Time | t _R | 1 | 8.3 | _ | ns | $V_{DS} = -4V$, $V_{GS} = -4.5V$, | |
| Turn-Off Delay Time | | | 47 | _ | ns | $R_G = 6\Omega$, $I_D = -1A$ | |
| Turn-Off Fall Time | t _F | | 20 | _ | ns | | |

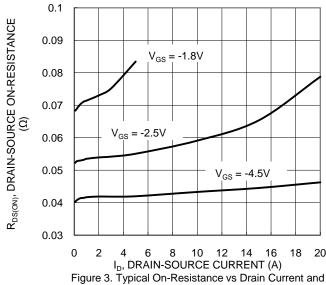
Notes:

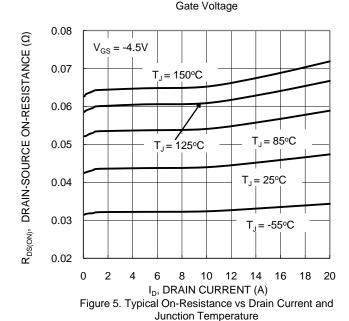
- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

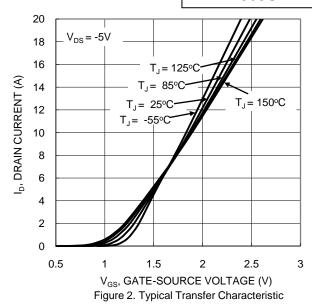


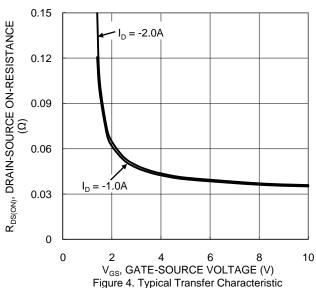












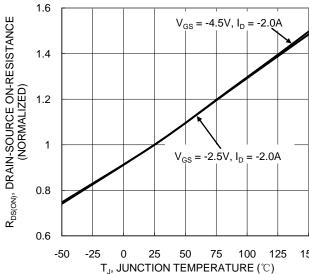


Figure 6. On-Resistance Variation with Junction Temperature



DMP2065UFDB

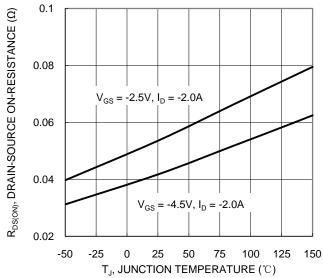


Figure 7. On-Resistance Variation with Junction Temperature

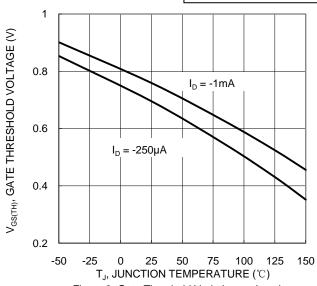
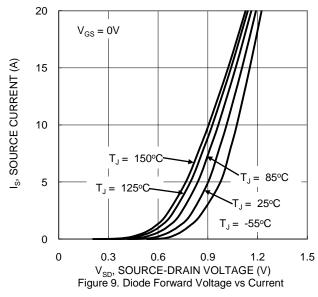
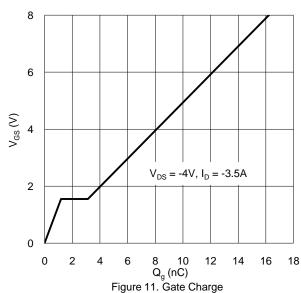
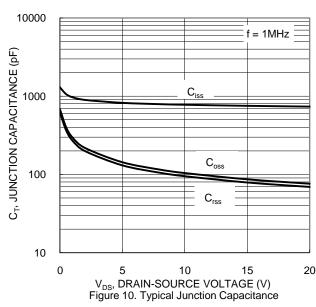
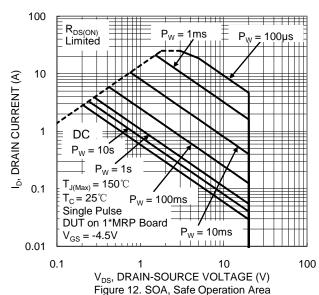


Figure 8. Gate Threshold Variation vs Junction Temperature











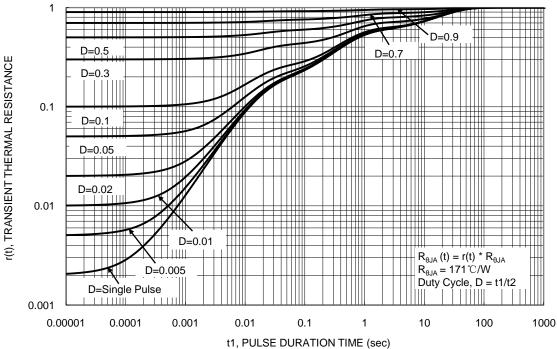


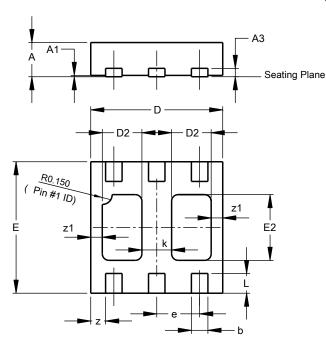
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)

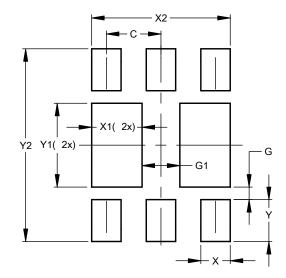


| U-DFN2020-6 Type B | | | | | | |
|-----------------------|-------|-------|-------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.545 | 0.605 | 0.575 | | | |
| A1 | 0.00 | 0.05 | 0.02 | | | |
| A3 | - | - | 0.13 | | | |
| b | 0.20 | 0.30 | 0.25 | | | |
| D | 1.95 | 2.075 | 2.00 | | | |
| D2 | 0.50 | 0.70 | 0.60 | | | |
| е | - | - | 0.65 | | | |
| Е | 1.95 | 2.075 | 2.00 | | | |
| E2 | 0.90 | 1.10 | 1.00 | | | |
| k | - | - | 0.45 | | | |
| L | 0.25 | 0.35 | 0.30 | | | |
| Z | - | - | 0.225 | | | |
| z1 | - | - | 0.175 | | | |
| All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type B)



| Dimensions | Value |
|---------------|---------|
| Dillielisions | (in mm) |
| С | 0.650 |
| G | 0.150 |
| G1 | 0.450 |
| Х | 0.350 |
| X1 | 0.600 |
| X2 | 1.650 |
| Υ | 0.500 |
| Y1 | 1.000 |
| Y2 | 2.300 |



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